PHE13005

Silicon diffused power transistor

Rev. 03 — 20 November 2009 | Product data sheet

1. Product profile

1.1 General description

High voltage, high speed NPN planar-passivated power switching transistor in a SOT78 plastic package intended for use in high frequency electronic lighting ballast applications

1.2 Features and benefits

- Fast switching
- High voltage capability of 700 V
- Low thermal resistance

1.3 Applications

- Electronic lighting ballasts

1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_C	collector current	DC; see Figure 3, 1 and 2	-	-	4	A
P_{tot}	total power dissipation	$T_{mb} \leq 25$ °C; see Figure 4	-	-	75	W
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$ V	-	-	700	V
Static characteristics						
h_{FE}	DC current gain	$I_C = 1$ A; $V_{CE} = 5$ V; $T_{mb} = 25$ °C; see Figure 11	12	20	40	
		$I_C = 2$ A; $V_{CE} = 5$ V; $T_{mb} = 25$ °C; see Figure 11	10	17	28	

2. Ordering information

Table 2. Ordering information

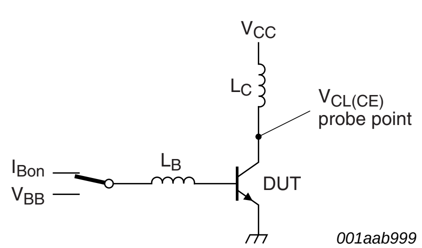
Type number	Package		
	Name	Description	Version
PHE13005	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

3. Limiting values

Table 3. Limiting values

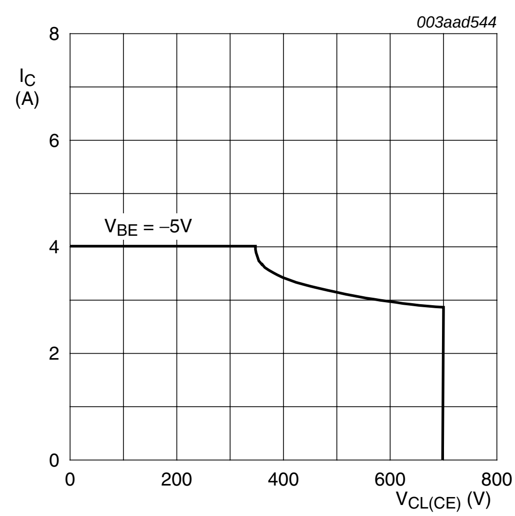
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CESM}	collector-emitter peak voltage	V_{BE} = 0 V	-	700	V
V_{CBO}	collector-base voltage	I_E = 0 A	-	700	V
V_{CEO}	collector-emitter voltage	I_B = 0 A	-	400	V
I_C	collector current	DC; see Figure 3, 1 and 2	-	4	A
I_{CM}	peak collector current		-	8	A
I_B	base current		-	2	A
I_{BM}	peak base current		-	4	A
P_{tot}	total power dissipation	T_{mb} ≤ 25 ℃; see Figure 4	-	75	W
T_{stg}	storage temperature		-65	150	℃
T_j	junction temperature		-	150	℃



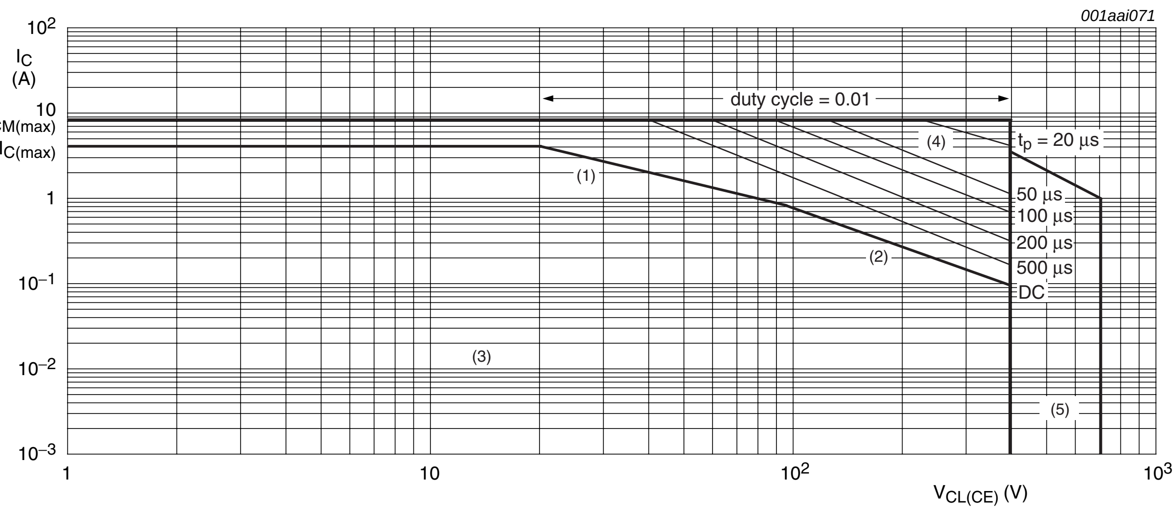
$$V_{CL(CE)} \le 1000\ V; V_{CC} = 150\ V; V_{BB} = -5\ V;$$
$$L_B = 1\ \mu H; L_C = 200\ \mu H$$

Fig 1. Test circuit for reverse bias safe operating area



$$T_j \le T_{j(max)}\ °C$$

Fig 2. Reverse bias safe operating area



$T_h \leq 25\ °C$ Mounted with heatsink compound and (30 ± 5)N force on the centre of the envelope

(1) P_{tot} maximum and P_{tot} peak maximum lines

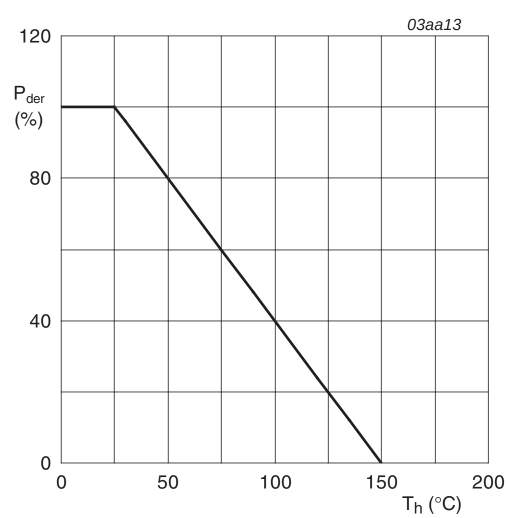
(2) Second breakdown limits

(3) Region of permissible DC operation

(4) Extension of operating region for repetitive pulse operation

(5) Extension of operating region during turn–on in single transistor converters provided that $R_{BE} \leq 100\ \Omega$ and $t_p \leq 0.6\ \mu s$

Fig 3. Forward bias safe operating area



$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig 4. Normalized total power dissipation as a function of heatsink temperature

4. Thermal characteristics

Table 4. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 5	-	-	1.67	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient		-	60	-	K/W

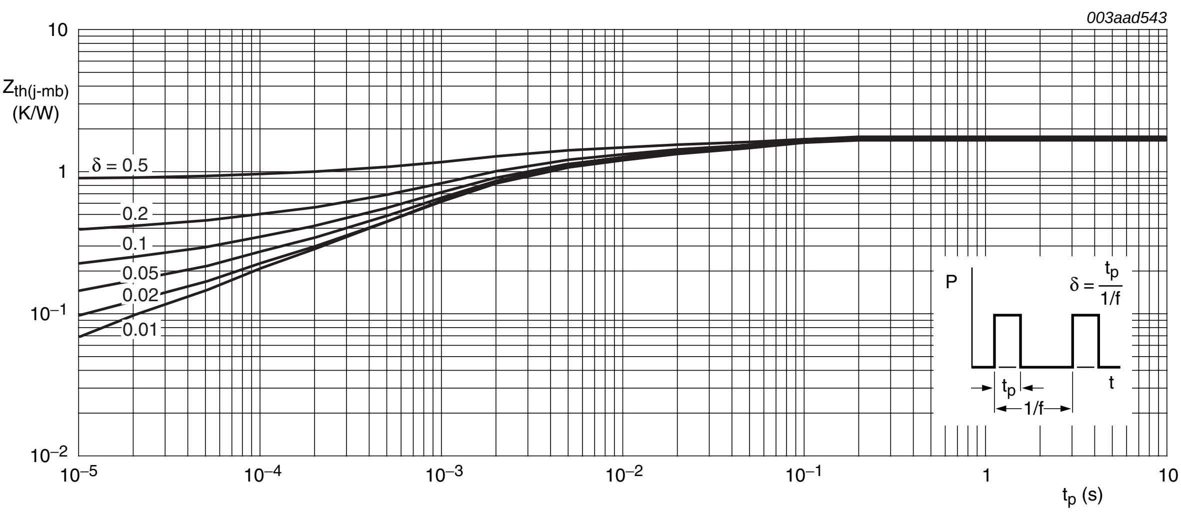


Fig 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

5. Characteristics

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
I_{CES}	collector-emitter cut-off current	V_{BE} = -1.5 V; V_{CE} = 700 V; T_j = 25 °C	-	-	1	mA
		V_{BE} = -1.5 V; V_{CE} = 700 V; T_j = 100 °C	-	-	5	mA
I_{CBO}	collector-base cut-off current	V_{CB} = 700 V; I_E = 0 A; T_{mb} = 25 °C	-	-	1	mA
I_{CEO}	collector-emitter cut-off current	V_{CE} = 400 V; I_B = 0 A; T_{mb} = 25 °C	-	-	0.1	mA
I_{EBO}	emitter-base cut-off current	V_{EB} = 9 V; I_C = 0 A; T_{mb} = 25 °C	-	-	1	mA
V_{CEOsus}	collector-emitter sustaining voltage	I_B = 0 A; I_C = 10 mA; L_C = 25 mH; T_{mb} = 25 °C; see Figure 6 and 7	400	-	-	V
V_{CEsat}	collector-emitter saturation voltage	I_C = 1 A; I_B = 0.2 A; T_{mb} = 25 °C; see Figure 8 and 9	-	0.1	0.5	V
		I_C = 2 A; I_B = 0.5 A; T_{mb} = 25 °C; see Figure 8 and 9	-	0.2	0.6	V
		I_C = 4 A; I_B = 1 A; T_{mb} = 25 °C; see Figure 8 and 9	-	0.3	1	V
V_{BEsat}	base-emitter saturation voltage	I_C = 1 A; I_B = 0.2 A; T_{mb} = 25 °C; see Figure 10	-	0.85	1.2	V
		I_C = 2 A; I_B = 0.5 A; T_{mb} = 25 °C; see Figure 10	-	0.92	1.6	V
h_{FE}	DC current gain	I_C = 1 A; V_{CE} = 5 V; T_{mb} = 25 °C; see Figure 11	12	20	40	
		I_C = 2 A; V_{CE} = 5 V; T_{mb} = 25 °C; see Figure 11	10	17	28	
Dynamic characteristics						
t_s	storage time	I_C = 2 A; I_{Bon} = 0.4 A; I_{Boff} = -0.4 A; R_L = 75 Ω; T_{mb} = 25 °C; resistive load; see Figure 12 and 13	-	2.7	4	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_{mb} = 25 °C; inductive load; see Figure 14 and 15	-	1.2	2	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_{mb} = 100 °C; inductive load; see Figure 14 and 15	-	1.4	4	µs
t_f	fall time	I_C = 2 A; I_{Bon} = 0.4 A; I_{Boff} = -0.4 A; R_L = 75 Ω; T_{mb} = 25 °C; resistive load; see Figure 12 and 13	-	0.3	0.9	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_{mb} = 25 °C; inductive load; see Figure 14 and 15	-	0.1	0.5	µs
		I_C = 2 A; I_{Bon} = 0.4 A; V_{BB} = -5 V; L_B = 1 µH; T_{mb} = 100 °C; inductive load; see Figure 14 and 15	-	0.16	0.9	µs

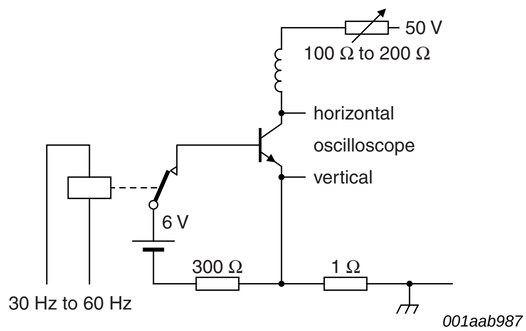


Fig 6. Test circuit for collector-emitter sustaining voltage

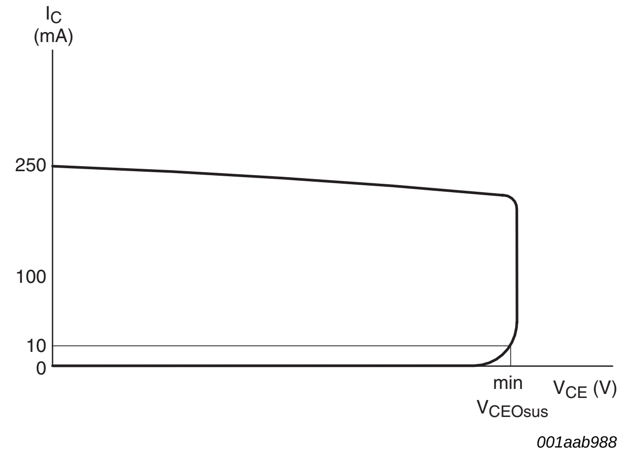
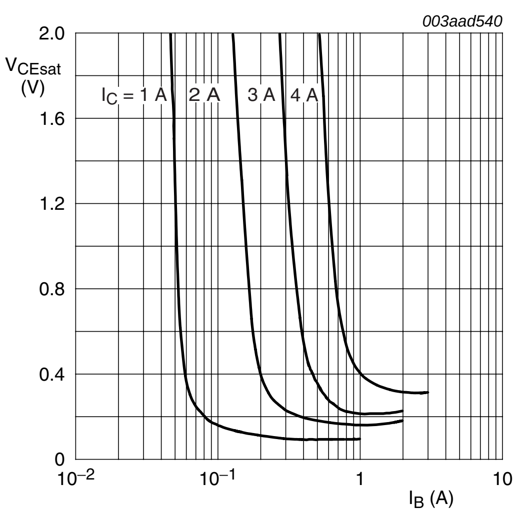
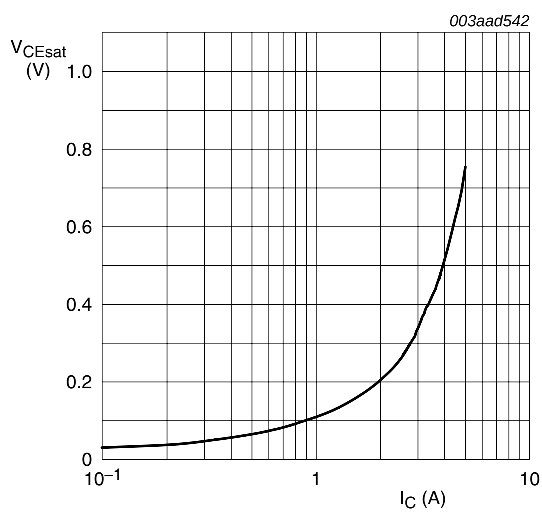


Fig 7. Oscilloscope display for collector-emitter sustaining voltage test waveform



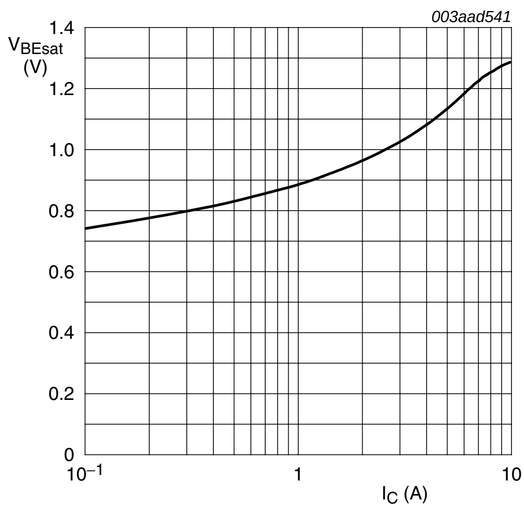
$T_j = 25\ °C$

Fig 8. Collector-emitter saturation voltage; typical values



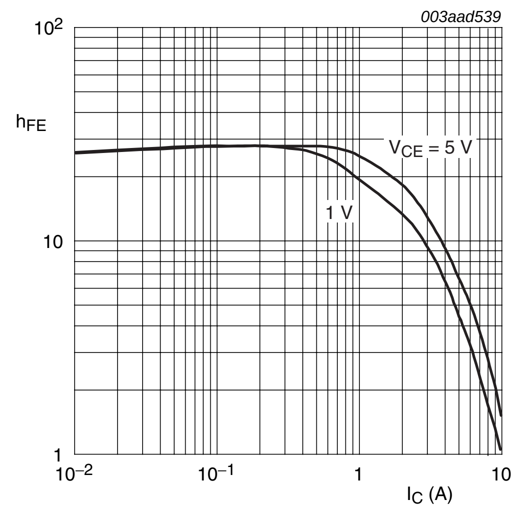
$$\frac{I_C}{I_B} = 4$$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



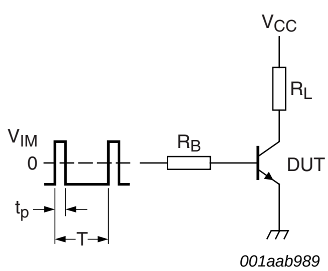
$$\frac{I_C}{I_B} = 4$$

Fig 10. Base-emitter saturation voltage; typical values



$$T_j = 25\ °C$$

Fig 11. DC current gain as a function of collector current; typical values



$$V_{IM} = -6 \text{ to } +8\ V; V_{CC} = 250\ V; t_p = 20\ \mu s; \delta = \frac{t_p}{T} = 0.01$$

R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig 12. Test circuit for resistive load switching

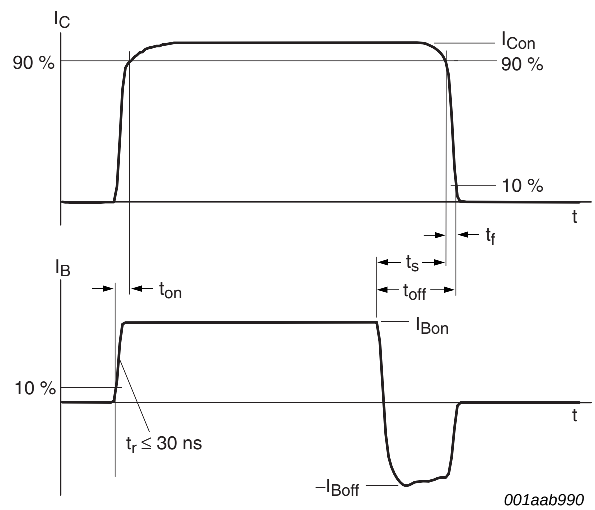
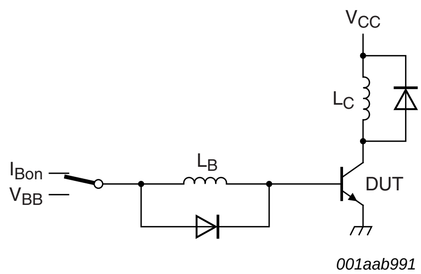


Fig 13. Switching times waveforms for resistive load



$V_{CC} = 300\ V; V_{BB} = -5\ V; L_C = 200\ \mu H; L_B = 1\ \mu H$

Fig 14. Test circuit for inductive load switching

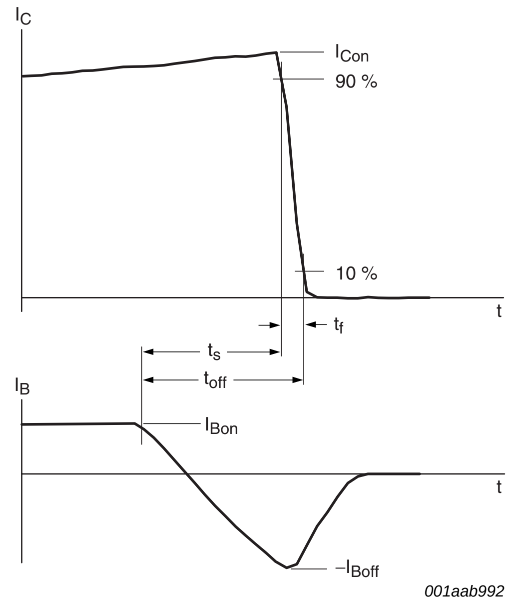
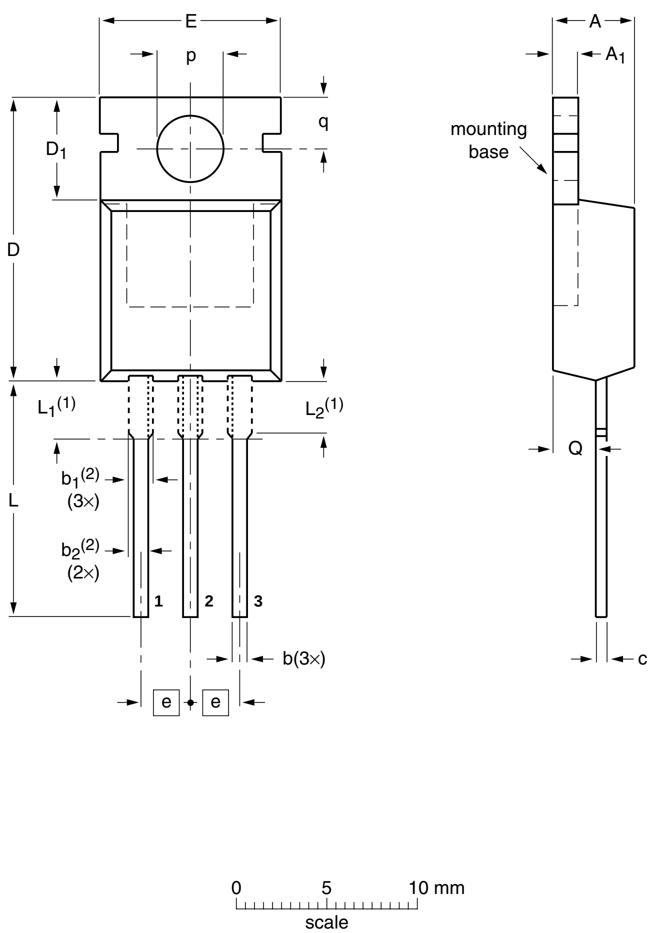


Fig 15. Switching times waveforms for inductive load

6. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB **SOT78**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1[2]	b_2[2]	c	D	D_1	E	e	L	L_1[1]	L_2[1] max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

1. Lead shoulder designs may vary.
2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			~~08-04-23~~ 08-06-13

Fig 16. Package outline SOT78 (TO-220AB)

7. Revision history

Table 6. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHE13005_3	20091120	Product data sheet	-	PHE13005_2
Modifications:	• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. • Legal texts have been adapted to the new company name where appropriate.			
PHE13005_2	19990201	Product specification	-	PHE13005_1
PHE13005_1	19980801	Preliminary specification	-	-

8. Legal information

8.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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10. Contents

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